

PROGRAM TIME TABLE

Wednesday, September 28						
9:30-12:15 Opening & Plenary Sessions (2F WINC HALL)						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
13:30-15:15 Area 6: A-1: GaN FET Technologies	13:30-15:15 Area 10&14: BL-1: Organic Photovoltaics (1)	13:30-15:15 Area 10: B-1: OLEDs	13:30-15:15 Area 2: C-1: Future Interconnect	13:30-15:10 Area 3: D-1: Modeling and Circuits	13:30-15:20 Area 1: E-1: Ge-MOS	13:30-15:00 Area 4: F-1: STT-RAM
15:40-16:55 Area 6: A-2: III-V HBTs and FETs	15:40-17:25 Area 10&14: BL-2: Organic Photovoltaics (2)	15:40-17:25 Area 10: B-2: Organic device fabrication process and interface control		15:40-17:00 Area 3: D-2: Device & Characteristics	15:45-17:15 Area 1: E-2: Characterization in Gate Stacks	15:40-17:30 Area 4: F-2: FeRAM/DRAM/SRAM
19:00-21:00 《Banquet/Young Researcher Award (16F, Tower Ball Room, Marriott Associa Hotel)》						
Thursday, September 29						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
		9:00-10:15 Area 10: B-3: Novel structure and fabrication process for OTFT	9:00-10:00 Area 2: C-3: Memory Application		9:00-10:20 Area 1: E-3: Process Technology and Analysis	9:00-10:00 Area 4: F-3: NAND
10:45-12:00 Short Presentation Area 6		10:45-12:00 Short Presentation Area 10	10:45-12:00 Short Presentation Area 2	10:45-12:00 Short Presentation Area 3	10:45-12:00 Short Presentation Area 1	10:45-12:00 Short Presentation Area 4
13:30-15:00 《Poster Session》 6F Exhibition Hall						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
15:25-16:25 Area 6: A-4: Novel III-V Devices and Applications	15:25-16:40 Area 8&13: KM-4: Nanowire Growth and Characterization	15:25-16:40 Area 10: B-4: Organic memory and photonic devices (1)	15:25-16:35 Area 2: C-4: Characterization (1)	15:25-16:45 Area 3: D-4: Tunnel-FET	15:25-16:55 Area 1: E-4: Junction Technology and Physics	15:25-16:25 Area 4: F-4: e-Flash
17:05-18:20 Area 6: A-5: Oxide Devices	17:05-18:20 Area 8&13: KM-5: Nanowire and Quantum Structures	17:05-18:20 Area 10: B-5: Organic memory and photonic devices (2)	17:05-18:25 Area 2: C-5: 3D Interconnect (1)	17:05-18:25 Area 3: D-5: Noise and Fluctuation	17:20-18:20 Area 1: E-5: Ge Metallization	17:05-18:05 Area 4: F-5: CT-Flash
19:00-21:00 《Rump Sessions》 5F Hall 1 “Opportunities and Challenges of Heterogeneous Integration on CMOS” - Photonics, MEMS, Sensors, etc - , 5F Hall 2 “Future Roadmap for Graphene Science and Technology”						
Friday, September 30						
5F Hall 1	5F Hall 2	10F 1002	10F 1003	11F 1101	11F 1102	11F 1103
9:00-10:45 Area 6&14: AL-6: SiC&GaN Power Switching Devices (1)	9:00-10:45 Area 8&13: KM-6: Graphene Synthesis	9:00-10:45 Area 10: B-6: Device physics and characterization of OTFT (1)		9:00-10:30 Area 3: D-6: Advanced CMOS Devices	9:00-10:20 Area 1: E-6: Ge Process Technology (1)	9:00-10:50 Area 4: F-6: PRAM/ReRAM (1)
11:15-12:30 Area 6&14: AL-7: SiC&GaN Power Switching Devices (2)	11:15-12:30 Area 8&13: KM-7: Graphene Application	11:15-12:30 Area 10: B-7: Device physics and characterization of OTFT (2)		11:15-12:25 Area 3: D-7: ET-SOI and Nanowire Devices	10:45-12:05 Area 1: E-7: Ge Process Technology (2)	11:15-12:40 Area 4: F-7: ReRAM (2)
14:00-15:30 Area 6: A-8: Processing and Characterization Technologies		14:00-15:45 Area 10: B-8: OTFT application (1)	14:00-15:50 Area 2: C-8: 3D Interconnect (2) and Characterization (2)	14:00-15:30 Area 3: D-8: Device Reliability	13:35-15:55 Area 1: E-8: III-V CMOS Technology	14:00-15:40 Area 4: F-8: ReRAM (3)
		16:10-17:25 Area 10: B-9: OTFT application (2)	16:10-17:30 Area 2: C-9: Characterization (3)		16:10-17:25 Area 1: E-9: Advanced Si Technology	16:10-17:10 Area 4: F-9: ReRAM (4)

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| <p>Area Scope</p> <ul style="list-style-type: none"> Area 1: Advanced LSI Processing & Materials Science Area 2: Advanced Interconnect / Materials Technology and Characterization Area 3: CMOS Devices / Device Physics Area 4: Advanced Memory Technology Area 5: Advanced Circuits and Systems | <ul style="list-style-type: none"> Area 6: Compound Semiconductor Electron Devices and Related Technologies Area 7: Photonic Devices and Optoelectronic Integration Area 8: Advanced Material Synthesis and Crystal Growth Technology Area 9: Physics and Application of Novel Functional Devices and Materials Area 10: Organic Materials Science, Device Physics, and Applications |
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9:30-12:15 Opening & Plenary Sessions (2F WINC HALL)							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
13:30-15:10 Area 5&11: GH-1: Image Sensor and MEMS Technology (1)		13:30-15:15 Area 7: I-1: Optical Link and Related Devices		13:30-15:15 Area 13: K-1: CNT Property	13:30-15:15 Area 14: L-1: Quantum Well& III-V Solar Cell	13:30-15:15 Area 8: M-1: Nitrides	
15:40-17:20 Area 5&11: GH-2: Image Sensor and MEMS Technology (2)		15:40-17:10 Area 7: I-2: Photonic Crystals		15:40-17:10 Area 13: K-2: CNT Device	15:40-17:25 Area 14: L-2: Thin-Film Silicon Solar Cells	15:40-17:25 Area 8: M-2: Oxides	
19:00-21:00 《Banquet/Young Researcher Award (16F, Tower Ball Room, Marriott Associa Hotel)》							
Thursday, September 29							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
9:00-10:15 Area 5: G-3: Variation and Reliability	9:00-10:15 Area 11: H-3: Electric, Magnetic and Optical Biosensing	9:00-10:15 Area 7: I-3: Plasmonics and Nonlinear Devices	9:00-10:15 Area 9: J-3: Graphene Quantum Transport	9:00-10:00 Area 13: K-3: Nanowire/Nanotube FET	9:00-10:15 Area 14: L-3: Compound Thin Film Solar Cells	9:00-10:15 Area 8: M-3: III-V Compounds	
10:45-12:00 Short Presentation Area 5	10:45-12:00 Short Presentation Area 11	10:45-12:00 Short Presentation Area 7	10:45-12:00 Short Presentation Area 9	10:45-12:00 Short Presentation Area 13	10:45-12:00 Short Presentation Area 14	10:45-12:00 Short Presentation Area 8	10:45-12:00 Short Presentation Area 12
13:30-15:00 《Poster Session》 6F Exhibition Hall							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
15:25-16:35 Area 5: G-4: Circuits for 3D Structure	15:25-16:40 Area 11: H-4: Neural Interface Technology	15:25-16:25 Area 7: I-4: Novel Optical Devices	15:25-16:40 Area 9: J-4: Advanced MOS-FETs and Transport				
17:05-18:20 Area 5: G-5: RF Circuits (1)		17:05-18:05 Area 7: I-5: Er-Doped Devices	17:05-18:20 Area 9: J-5: MEMS & Thin-Film Devices				
19:00-21:00 《Rump Sessions》 5F Hall 1 “Opportunities and Challenges of Heterogeneous Integration on CMOS” - Photonics, MEMS, Sensors, etc - , 5F Hall 2 “Future Roadmap for Graphene Science and Technology”							
Friday, September 30							
11F 1104	11F 1107	12F 1201	12F 1202	12F 1203	12F 1204	12F 1207	12F 1208
9:00-10:50 Area 5: G-6: Analog and Digital Circuits	9:00-10:45 Area 11: H-6: Micro Fabrication and Micro fluidic Devices	9:00-10:45 Area 2&7: CI-6: Optical Interconnect (1)	9:00-10:45 Area 9: J-6: Photon & Spin in Nanostructures				9:00-10:45 Area 12: N-6: Spintronics materials and devices
11:15-12:35 Area 5: G-7: RF Circuits (2)	11:15-12:15 Area 11: H-7: Nano fabrication and Application	11:15-12:25 Area 2&7: CI-7: Optical Interconnect (2)	11:15-12:30 Area 9: J-7: Quantum Transport in Nanostructures				11:15-12:30 Area 12: N-7: Spin transport in semiconductors
		14:00-15:30 Area 7: I-8: SiGe-Based Optical Devices	14:00-15:45 Area 9: J-8: Qubit and Novel Functional Devices	14:00-15:45 Area 13: K-8: Graphene Property	14:00-15:45 Area 14: L-8: Power Devices & ICs	14:00-15:45 Area 8: M-8: Growth techniques of Si and Ge	14:00-15:30 Area 12: N-8: Circuit application of spintronics devices
		16:10-17:25 Area 7: I-9: Quantum-Dot Devices		16:10-17:25 Area 13: K-9: Graphene Device	16:10-17:25 Area 14: L-9: Novel Concepts	16:10-17:10 Area 8: M-9: Characterization of group IV related materials	16:10-17:25 Area 12: N-9: Physics of spintronics devices

Area 11: Micro/Nano Electromechanical Systems and Bio/Medical Analyses
 Area 12: Spintronics Materials and Devices
 Area 13: Application of Nanotubes, Nanowires, and Graphene
 Area 14: Photovoltaics & Power Semiconductor Devices